论文

基于非线性介电薄膜的电调滤波器优化设计

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摘要 采用脉冲激光沉积(PLD)法在(001)MgO基片上制备出高质量的SrTiO3(STO)薄膜,构建了Au/STO/MgO结构的叉指电容。在77K、10KHz条件下,对叉指电容的特性进行了测试,结果表明:在40kV/cm的直流电场作用下,电容值从1.75 pF减小为1.25 pF,电容值的相对变化率为28.5%。在此基础上,根据多层介质叉指电容保角变换模型。定量计算和仿真了STO薄膜的介电常数和微波频率下叉指电容的性能参数,并由此设计了一个三阶带通滤波器,该滤波器可实现13 50%的中心频率移动。

关键词 STO 薄膜 介电性质 叉指电容 滤波器

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Optimized design of electrically tunable filter based on nonlinear dielectric film

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Abstract Excellent (001) SrTiO3 (STO) thin films were grown on (001) MgO substrates by pulsed laser deposition (PLD) method. Interdigital capacitors (IDC) were fabricated on the STO films. When the electric field increases from 0 kV/cm to 40 kV/cm, the capacitance drops from 1.75 pF to 1.25 pF at 77K and 10kHz. The permittivity ϵ r of STO films were calculated by the conformal mapping-based models. A three-pole bandpass filter based on the IDC was designed. Excellent performances of the filter are achieved.

Key words STO thin film dielectric properties IDC filter

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